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(71) Applicant: **INTEL CORPORATION (a Delaware Corporation)** [US/US]; 2200 Mission College Boulevard, Santa Clara, CA 95052 (US).

(72) Inventors: **WONG, Lawrence**; 265 NW Silverado Drive, Beaverton, OR 97006 (US). **MORROW, Patrick**; 6150 NW simmasho Drive, Portland, OR 97229 (US). **LEU, Jih-perng**; 14606 N.W. Applegate Lane, Portland, OR 97229 (US). **OTT, Andrew**; 934 N.E. Simmental Street, Hillsboro, OR 97124 (US). **KLOSTER, Grant**; 14390 Camden Lane, Lake Oswego, OR 97035 (US).

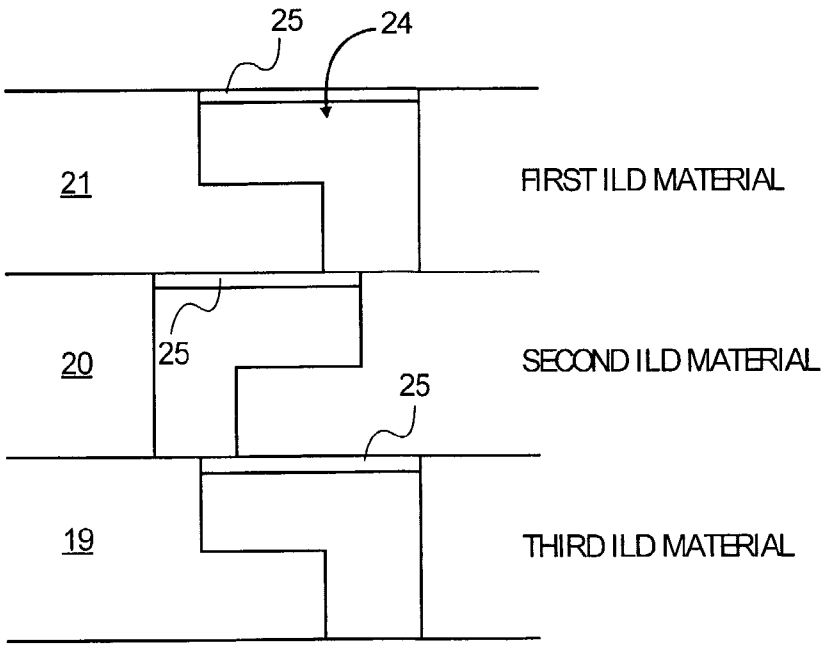
(74) Agents: **MALLIE, Michael, J.** et al.; Blakely, Sokoloff, Taylor & Zafman, 7th Floor, 12400 Wilshire Boulevard, Los Angeles, CA 90025 (US).

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(54) Title: DUAL-DAMASCENE INTERCONNECTS WITHOUT AN ETCH STOP LAYER BY ALTERNATING ILDS



(57) Abstract: A dual damascene process where first alternate ILDs (19, 21, 30, 32) are made of a first material and second alternate ILDs (20, 31, 33) are made of a second material. Each material is etchable at a faster rate than the other in the presence of different etchant such as for an organic polymer and an inorganic low K material. This allows the ILDs to be deposited alternately on one another without an etchant stop layer thereby reducing capacitance.

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